

- 20 W Pulsed Power Dissipation
- 100 V Capability
- 2 A Continuous Collector Current
- 4 A Peak Collector Current

LP PACKAGE
(TOP VIEW)

MDTRAB

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	TIPP115 TIPP116 TIPP117	V_{CBO}	-60 -80 -100
Collector-emitter voltage ($I_B = 0$)	TIPP115 TIPP116 TIPP117	V_{CEO}	-60 -80 -100
Emitter-base voltage	V_{EBO}	-5	V
Continuous collector current	I_C	-2	A
Peak collector current (see Note 1)	I_{CM}	-4	A
Continuous base current	I_B	-50	mA
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)	P_{tot}	0.8	W
Pulsed power dissipation (see Note 3)	P_T	20	W
Operating junction temperature range	T_j	-55 to +150	°C
Storage temperature range	T_{stg}	-55 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds	T_L	260	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.
 2. Derate linearly to 150°C case temperature at the rate of 0.32 W/°C.
 3. $V_{CE} = 20$ V, $I_C = 1$ A, $P_W = 10$ ms, duty cycle $\leq 2\%$.

PRODUCT INFORMATION

electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage (see Note 4)	$I_C = -10 \text{ mA}$	$I_B = 0$	TIPP115 TIPP116 TIPP117	-60 -80 -100		V
I_{CEO}	Collector-emitter cut-off current	$V_{CE} = -30 \text{ V}$ $V_{CE} = -40 \text{ V}$ $V_{CE} = -50 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	TIPP115 TIPP116 TIPP117		-2 -2 -2	mA
I_{CBO}	Collector-base cut-off current	$V_{CE} = -60 \text{ V}$ $V_{CE} = -80 \text{ V}$ $V_{CE} = -100 \text{ V}$	$I_B = 0$ $I_B = 0$ $I_B = 0$	TIPP115 TIPP116 TIPP117		-1 -1 -1	mA
I_{EBO}	Emitter cut-off current	$V_{EB} = -5 \text{ V}$	$I_C = 0$			-2	mA
h_{FE}	Forward current transfer ratio	$V_{CE} = -4 \text{ V}$ $V_{CE} = -4 \text{ V}$	$I_C = -1 \text{ A}$ $I_C = -2 \text{ A}$	(see Notes 4 and 5)	1000 500		
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_B = -8 \text{ mA}$	$I_C = -2 \text{ A}$	(see Notes 4 and 5)		-2.5	V
V_{BE}	Base-emitter voltage	$V_{CE} = -4 \text{ V}$	$I_C = -2 \text{ A}$	(see Notes 4 and 5)		-2.8	V
V_{EC}	Parallel diode forward voltage	$I_E = -4 \text{ A}$	$I_B = 0$	(see Notes 4 and 5)		-3.5	V

NOTES: 4. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

5. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

PRODUCT INFORMATION